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## Structure, band offsets and photochemistry at epitaxial $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>/ $\alpha$ -Fe<sub>2</sub>O<sub>3</sub> heterojunctions

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### 11 Abstract

12 We test the hypothesis that electron–hole pair separation following light absorption enhances photochemistry at  
13 oxide/oxide heterojunctions which exhibit a type II or staggered band alignment. We have used hole-mediated photo-  
14 decomposition of trimethyl acetic acid chemisorbed on surfaces of heterojunctions made from epitaxial  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub> on  $\alpha$ -  
15 Fe<sub>2</sub>O<sub>3</sub>(0001) to monitor the effect of UV light of wavelength 385 nm (3.2 eV) in promoting photodissociation. Absorp-  
16 tion of photons of energies between the bandgaps of  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub> ( $E_g = 4.8$  eV) and  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub> ( $E_g = 2.1$  eV) is expected to be  
17 strong only in the  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub> layer. The staggered band alignment should then promote the segregation of holes (elec-  
18 trons) to the  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub> ( $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>) layer. Surprisingly, we find that the  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub> surface alone promotes photodissociation  
19 of the molecule at  $h\nu = 3.2$  eV, and that any effect of the staggered band alignment, if present, is masked. We propose  
20 that the inherent photoactivity of the  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>(0001) surface results from the creation of bound excitons in the surface  
21 which destabilize the chemisorption bond in the molecule, resulting in photodecomposition.  
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23 **Keywords:** Photocatalysis; Heterojunctions; Epitaxial

### 25 1. Introduction

26 Heterogeneous photocatalysis on oxide surfaces  
27 represents a rich field of study that is both funda-

mentally interesting and important for a variety of 28  
technologies. For example, photocleaning is a rapidly 29  
developing technology in which electron–hole 30  
pair creation at the surface of a thin TiO<sub>2</sub> coating 31  
on window glass results in photochemical decom- 32  
position of adsorbed organic contaminants. The 33  
fundamentals of this and related processes are 34  
not only fascinating, but also essential to under- 35

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stand in order to advance the technology [1]. The heterogeneous photocatalytic activity of  $\text{TiO}_2$  has been studied in some detail [2]. That of other oxides, such as  $\alpha\text{-Cr}_2\text{O}_3$  and  $\alpha\text{-Fe}_2\text{O}_3$ , has generally been avoided. Thiel et al. [3] investigated the role of surface vibrations on the photochemistry of NO on a thin epitaxial film of  $\alpha\text{-Cr}_2\text{O}_3(0001)$  grown on Cr(110). The photochemistry of  $\text{Fe}_2\text{O}_3$  particles in aqueous solutions [4,5] and in the gas phase [6] has also been studied to a limited extent. One reason the oxides of Fe and Cr have generally been avoided is that conventional wisdom suggests that d-states in the band gap of these materials may act as trapping sites and/or electron–hole ( $e^-/h^+$ ) pair recombination centers, thereby reducing heterogeneous photocatalytic activity.

In principle,  $e^-/h^+$  pair lifetimes can be enhanced by spatial separation of charges via a heterojunction in which the band edges are staggered. While some work has been done on the photocatalytic activity of  $\alpha\text{-Fe}_2\text{O}_3$  in a heterojunction structure, this work primarily involved small particles in solution consisting of at least two layers of different oxides [7]. This work, while more reflective of real-world conditions, nevertheless does little to yield insight into photochemical mechanisms and the impact of the heterojunction structure. A multitude of experimental variables, many of which are uncontrolled, preclude determination of specific cause-and-effect relationships. To gain fundamental understanding it is often necessary to simplify and define the system sufficiently well that the number of experimental variables is limited. To this end, we have examined the effect of oxide heterojunction formation on photocatalytic activity using epitaxial films of  $\alpha\text{-Cr}_2\text{O}_3$  and  $\alpha\text{-Fe}_2\text{O}_3$  grown and studied entirely in a UHV environment. The  $\alpha\text{-Cr}_2\text{O}_3/\alpha\text{-Fe}_2\text{O}_3(0001)$  system was chosen because it is readily grown by oxygen plasma assisted molecular beam epitaxy, and exhibits a staggered, albeit noncommutative band alignment [8]. A noncommutative band alignment is one in which the band offset for A on B is different from that of B on A. The noncommutativity was tentatively assigned to a difference in interface structure for  $\alpha\text{-Cr}_2\text{O}_3$  grown on  $\alpha\text{-Fe}_2\text{O}_3$  compared to  $\alpha\text{-Fe}_2\text{O}_3$  grown on  $\alpha\text{-Cr}_2\text{O}_3$ , with the resulting change in interface dipole. Subsequent theoretical

calculations supported this conclusion and yielded plausible differences in interface structure that would lead to the observed band offset noncommutativity [9]. Inasmuch as staggered semiconductor band alignments are known to be effective at separating  $e^-/h^+$  pairs created by the absorption of sub-bandgap light [10], we investigate in the present work the hypothesis that photochemistry can be carried out to a greater extent on such a heterojunction than is possible on the surface of either material in isolation.

The remainder of the paper is organized as follows. Following experimental details in Section 2, we present in Section 3 new results on the abruptness of the interface and the dependence of band offset on growth temperature. In addition, we present new results which refine and strengthen the band offset analysis discussed originally in Ref. [8]. In Section 4, we discuss hole-mediated photodecomposition of trimethyl acetate (TMA) adsorbed on  $\alpha\text{-Cr}_2\text{O}_3/\alpha\text{-Fe}_2\text{O}_3$  heterojunctions and the associated free surfaces of the pure materials, and we summarize in Section 5.

## 2. Experimental

Film growth by oxygen plasma assisted molecular beam epitaxy (OPAMBE), X-ray photoelectron spectroscopy (XPS) measurements, and all photodesorption experiments were performed in separate custom ultrahigh vacuum (UHV) chambers connected by a custom UHV sample transfer system [11]. All epitaxial films and heterojunctions were grown on  $\alpha\text{-Al}_2\text{O}_3(0001)$  substrates cleaned by room temperature exposure to activated oxygen for thirty minutes. Reference surfaces of  $\alpha\text{-Cr}_2\text{O}_3$  film were grown directly on  $\alpha\text{-Al}_2\text{O}_3(0001)$ , and were typically 600 Å thick. Reference surfaces of  $\alpha\text{-Fe}_2\text{O}_3$  film were typically 1100 Å thick, and were grown on a 100 Å-thick  $\alpha\text{-Cr}_2\text{O}_3$  buffer layer to mitigate the large in-plane lattice mismatch between  $\alpha\text{-Fe}_2\text{O}_3$  and the  $\alpha\text{-Al}_2\text{O}_3$  substrate ( $\Delta a/a = 5.80\%$  and  $3.36\%$  for  $\alpha\text{-Fe}_2\text{O}_3/\alpha\text{-Al}_2\text{O}_3(0001)$  and  $\alpha\text{-Cr}_2\text{O}_3/\alpha\text{-Al}_2\text{O}_3(0001)$ , respectively). Heterojunctions consisting of a few to several monolayers (ML) of  $\alpha\text{-Cr}_2\text{O}_3$  were prepared on reference surfaces of  $\alpha\text{-Fe}_2\text{O}_3(0001)$ , as described above. In situ

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129 thickness calibration of the  $\text{Cr}_2\text{O}_3$  ML was  
130 achieved by relating the period of reflection high-  
131 energy electron diffraction (RHEED) intensity  
132 oscillations observed during the growth of the  
133  $\text{Cr}_2\text{O}_3$  buffer layer with the Cr flux measured by  
134 atomic absorption (AA) spectroscopy [8]. The  
135  $\text{Cr}_2\text{O}_3$  films were then grown for a period of time  
136 corresponding to some multiple of the RHEED  
137 intensity oscillation period ( $\sim 15$  s) at the same  
138 AA value. The substrate temperature was varied  
139 from 500 to 800 °C.

140 Immediately after film growth and before dos-  
141 ing with trimethyl acetic acid (TMAA), XPS with  
142 monochromatic  $\text{AlK}\alpha$  X-rays was carried out at  
143 a take-off angle ( $\theta_i$ ) of  $12^\circ$  relative to the surface  
144 plane to check for surface carbon contamination  
145 and to identify the surface termination.  $\alpha$ -  
146  $\text{Fe}_2\text{O}_3(0001)$  films grown under OPAMBE condi-  
147 tions are Fe-terminated [12], while  $\alpha$ - $\text{Cr}_2\text{O}_3$   
148 (0001) films can be either Cr or chromyl-termi-  
149 nated [13], depending on the amount of oxygen  
150 present in the chamber during cool down follow-  
151 ing growth [14]. Chromyl termination of the  
152  $\text{Cr}_2\text{O}_3(0001)$  surface can be detected as a high-  
153 binding energy shoulder on the lattice oxygen peak  
154 in a high-resolution O 1s XPS spectrum collected  
155 at grazing emission [14]. Charge neutralization  
156 by low-energy (1–2 eV) electron bombardment  
157 from a flood gun was necessary during XPS be-  
158 cause of the insulating nature of these materials.  
159 Thus, the measured binding energies were not  
160 absolute as measured, and all spectra were ad-  
161 justed so the lattice O 1s binding energy was  
162 530.0 eV.

163 TMA C and O 1s core-level spectra were mea-  
164 sured after dosing with TMAA, but prior to UV  
165 irradiation and photodesorption measurements.  
166 These measurements were then repeated after UV  
167 irradiation. The stability of the adsorbed molecule  
168 with respect to X-ray flux and flood gun bombard-  
169 ment in XPS was found to be excellent, even for  
170 several hours of analysis. The standard TMAA  
171 dose ranged from 12 L for  $\text{Fe}_2\text{O}_3$  up to 1200 L  
172 for  $\text{Cr}_2\text{O}_3$ , and was found to result in saturation  
173 of the different surfaces. Here, we have assumed  
174 an enhancement factor of  $\sim 100$  from the direc-  
175 tional doser we employed. All dosing, analysis  
176 and photodesorption experiments were performed

with the specimen at  $\sim 300$  K. A chopped 100 W  
Hg arc lamp with a water-filled infrared filter, a  
collimating lens, and a cut-off filter which removed  
all emission lines of wavelength less than 385 nm  
was used as the photoexcitation source. After pass-  
ing through the lens, the lamp spot size was  $\sim 1$  cm  
in diameter, matching the sample size. TMA pho-  
todesorption was monitored in real-time using a  
shielded residual gas analyzer.

Electron microscopy observations and electron  
energy loss spectroscopy (EELS) were carried out  
*ex situ* in a scanning transmission electron micro-  
scope (STEM) VG Microscopes HB501UX oper-  
ated at 100 kV and equipped with a Nion  
aberration corrector and a parallel electron energy  
loss spectrometer. This microscope is capable of  
routinely achieving a spatial resolution of  
0.13 nm. Cross sectional samples for STEM were  
prepared by conventional methods: grinding, dim-  
pling and Ar ion milling at 5 kV.

### 3. Interface abruptness and band offsets

The common corundum crystal structure of  $\alpha$ -  
 $\text{Cr}_2\text{O}_3$  and  $\alpha$ - $\text{Fe}_2\text{O}_3$  together with the fact that  
Cr(III) and Fe(III) have similar ionic radii suggests  
that  $\alpha$ - $\text{Cr}_2\text{O}_3$  and  $\alpha$ - $\text{Fe}_2\text{O}_3$  should exhibit a high de-  
gree of miscibility. However, we have found that  
the interface between these two materials is rather  
abrupt. We show in Fig. 1 STEM images of a  
 $\alpha$ - $\text{Cr}_2\text{O}_3/\alpha$ - $\text{Fe}_2\text{O}_3/\alpha$ - $\text{Cr}_2\text{O}_3/\alpha$ - $\text{Al}_2\text{O}_3(0001)$  multilayer  
stack grown at 600 °C. The low-resolution image  
shown in Fig. 1a reveals a high degree of flatness  
for each film, as well as an apparent abruptness  
of each interface. The higher resolution images in  
Fig. 1b and c reveal the cation rows in three mate-  
rials, and the contrast is suggestive of abrupt inter-  
faces. In Fig. 2a we show electron energy loss  
spectra as a function of position along a line nor-  
mal to the  $\alpha$ - $\text{Cr}_2\text{O}_3/\alpha$ - $\text{Fe}_2\text{O}_3$  interface. The Cr  $L_{2,3}$   
edge loss feature diminishes and the Fe  $L_{2,3}$  edge  
feature grows as the interface is crossed in passing  
from  $\alpha$ - $\text{Cr}_2\text{O}_3$  to  $\alpha$ - $\text{Fe}_2\text{O}_3$ . The integrated areas un-  
der the two metal L-edge loss features are plotted  
against distance along the normal line in Fig. 2b.  
From these data, the *apparent* width of the inter-  
face is  $\sim 10$  Å, or 4 ML of  $\text{M}_2\text{O}_3$ . However, there

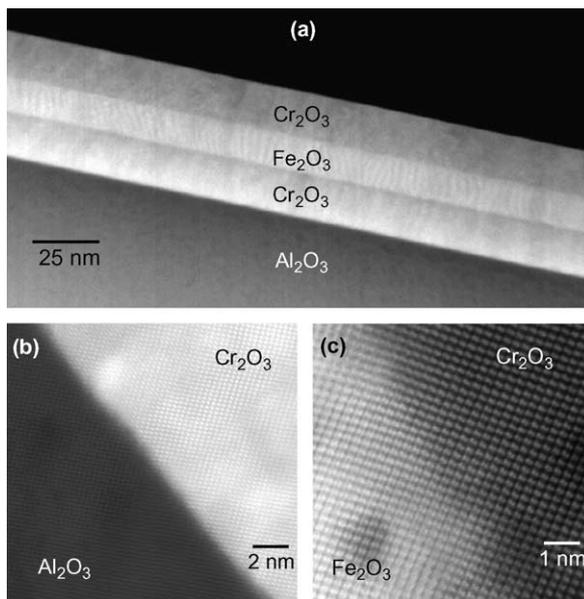


Fig. 1. STEM images of an epitaxial  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>/ $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>/ $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>/ $\alpha$ -Al<sub>2</sub>O<sub>3</sub>(0001) layered specimen.

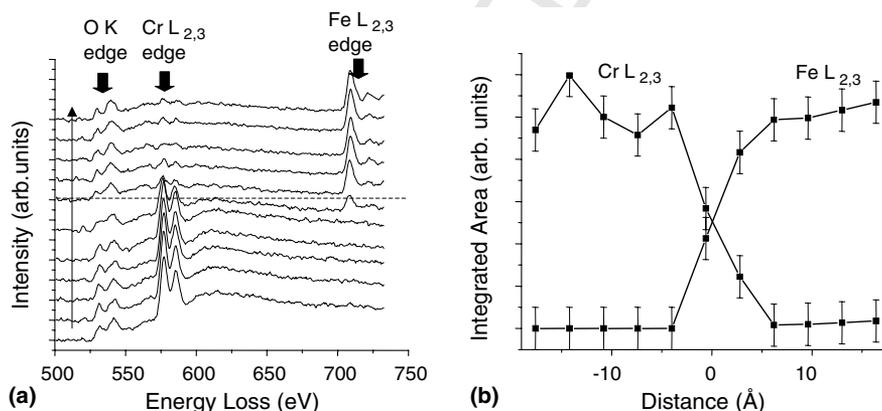


Fig. 2. (a) Energy loss spectra taken along a line normal to the interface of  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub> and  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub> and (b) integrated areas under the Cr L<sub>2,3</sub> and Fe L<sub>2,3</sub> loss features as a function of distance from the interface.

222 is a finite interaction volume for the electron beam,  
 223 so the actual interface width is less than 10 Å. From  
 224 these data, along with the Z-contrast images in Fig.  
 225 1, we conclude that the interface is quite abrupt,  
 226 with intermixing extending to no more than  
 227  $\pm 1$  ML from the interface. This result is crucial be-  
 228 cause intermixing defines the composition and  
 229 structure of the interface and, thus, the interface di-  
 230 pole potential, which is one term in the band offset.

The valence band offset can be determined from 231  
 core-level and valence band binding energies for  $\alpha$ - 232  
 Cr<sub>2</sub>O<sub>3</sub>,  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>, and heterojunctions (HJ) of the 233  
 two from the formula, 234

$$\Delta E_v = (E_{\text{Fe}3p} - E_v)_{\text{Fe}_2\text{O}_3} - (E_{\text{Cr}3p} - E_v)_{\text{Cr}_2\text{O}_3} - (E_{\text{Fe}3p} - E_{\text{Cr}3p})_{\text{HJ}} \quad (1)$$

The subscript HJ refers to the heterojunction 238  
 consisting of  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub> on  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>. We plot in 239

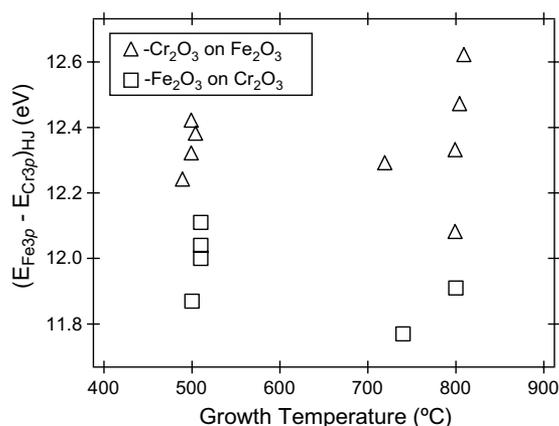


Fig. 3. Shallow core-level binding energy difference ( $E_{\text{Fe}3p} - E_{\text{Cr}3p}$ ) vs. growth temperature for epitaxial  $\alpha\text{-Cr}_2\text{O}_3/\alpha\text{-Fe}_2\text{O}_3$  heterojunctions. The valence band offset depends linearly on this quantity.

due to the similarity in atomic number for Cr and Fe.

A recent exchange in the literature raised the issue of how best to determine the valence band maximum (VBM) from XPS measurements of the valence band spectra of oxides. Accurate determination of the VBM ( $E_v$  in Eq. (1)) is of critical importance to finding the quantities  $(E_{\text{Fe}3p} - E_v)_{\text{Fe}}$  and  $(E_{\text{Cr}3p} - E_v)_{\text{Cr}}$  with sufficient accuracy to obtain accurate values of the valence band offset (VBO). McKee et al. [15] argue that the most accurate method for finding the VBM involves fitting a theoretical VB density of states (VB DOS), calculated from density functional theory (DFT) and convolved with a Gaussian to simulate the effects of instrumental broadening, to the experimental spectrum. The VBM is then equated with the energy at which the unbroadened VB DOS goes to zero. This approach is the same as that originally taken by Kraut et al. [16,17], who used this method to find band offsets for HJs of more covalent semiconductors. In contrast, Chambers et al. [18,19] argue that DFT is not sufficiently accurate for this task when applied to oxides, even though the procedure works very well for more covalent semiconductors such as Si, Ge and III-Vs. We argue that a more accurate method involves finding the intercept between a line fit to the VB leading edge with one fit to the background between the VBM and the Fermi level—the so-called linear method [18,19]. The error incurred by using Kraut's method with DFT theory is  $\sim 0.5$  eV for oxides such as SrO, TiO<sub>2</sub> and SrTiO<sub>3</sub> [19]. We show that if a more accurate self-consistent GW theory is used, agreement between theory and experiment is much better, and the difference between Kraut's method and the linear method is within experimental uncertainty (a few hundredths of an eV) [18].

We draw similar conclusions here for  $\alpha\text{-Cr}_2\text{O}_3$  and  $\alpha\text{-Fe}_2\text{O}_3$ . We show in Fig. 4 fits of the experimental VB spectra for  $\alpha\text{-Cr}_2\text{O}_3$  and  $\alpha\text{-Fe}_2\text{O}_3$  after background subtraction (open circles) to VB DOS generated by DFT (solid curves) in the generalized gradient approximation (GGA). The raw VB DOS have been broadened by convolution with Gaussians of width equal to 0.46 eV, the experimental resolution used in these measurements. The binding energy scales are relative to the energies at

240 Fig. 3 the quantity  $(E_{\text{Fe}3p} - E_{\text{Cr}3p})_{\text{HJ}}$  for hetero-  
 241 junctions, in which the thickness of the top layer  
 242 was  $\sim 15$  Å, as a function of growth temperature.  
 243 As seen in Fig. 3, the HJs grown at 500 °C, for  
 244 which the interfaces are as abrupt as those shown  
 245 in Figs. 1 and 2, the  $(E_{\text{Fe}3p} - E_{\text{Cr}3p})_{\text{HJ}}$  values tend  
 246 to fall into narrow bands centered at  $12.00 \pm 0.15$   
 247 and  $12.35 \pm 0.10$  eV for the two kinds of HJs, in  
 248 excellent agreement with previous results [8].  
 249 Increasing the growth temperature to 800 °C  
 250 causes the  $(E_{\text{Fe}3p} - E_{\text{Cr}3p})_{\text{HJ}}$  values to disperse  
 251 slightly more, in keeping with expected slightly  
 252 greater extents of intermixing, and less well-con-  
 253 trolled interface composition at the higher growth  
 254 temperature. Nevertheless, the noncommutativity  
 255 in the valence band offset is still present at a  
 256 growth temperature of 800 °C, revealing that dif-  
 257 ferences in interface composition and structure re-  
 258 main in tact for the two growth sequences.  
 259 Previous theoretical calculations suggest that  
 260 growing Cr<sub>2</sub>O<sub>3</sub> on Fe<sub>2</sub>O<sub>3</sub> results in the formation  
 261 of a “split-metal” interface, as depicted in Fig. 7  
 262 [9]. In contrast, growth of the inverted interface  
 263 was predicted to result in an “oxygen-divided”  
 264 interface, in which a close-packed layer of O an-  
 265 ions defines the interface, and two 1/3 ML of Fe  
 266 (Cr) are above (below) this O layer. Unfortunately,  
 267 it is not possible to distinguish between these two  
 268 interface structures with current TEM technology

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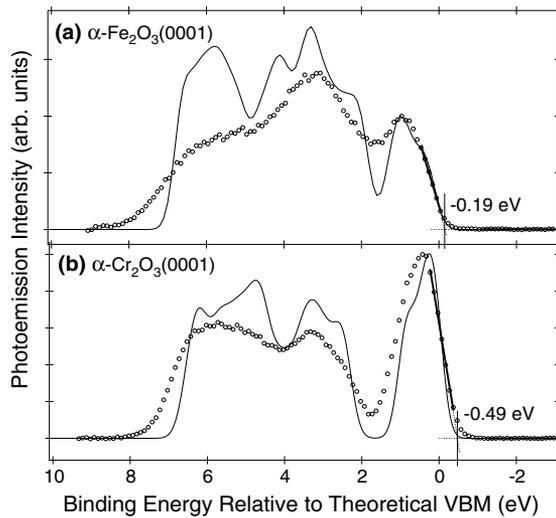


Fig. 4. Valence band photoemission spectra (open circles) for epitaxial: (a)  $\alpha\text{-Fe}_2\text{O}_3(0001)$ , and (b)  $\alpha\text{-Cr}_2\text{O}_3(0001)$ , along with theoretical VBDOS (solid curve) computed from DFT GGA and broadened by convolving with a Gaussian of width equal to 0.46 eV to simulate instrumental resolution. The theoretical VBM is the energy at which the unbroadened theoretical VBDOS goes to zero. Also shown is the VBM determined by extrapolating the leading edge of the experimental VB spectrum to background.

317 which the unbroadened VBDOS go to zero, which  
 318 are by definition the theoretical VBM for the two  
 319 materials. The fit between broadened theory and  
 320 experiment is not particularly good for either  
 321 oxide. In both cases, the overall width of the VB  
 322 is smaller in theory than in experiment, and the  
 323 calculated VB leading edges rise more rapidly than  
 324 their experimental counterparts. These two short-  
 325 comings are most likely due to the fact that DFT  
 326 predicts d-states that are too shallow relative to  
 327 experiment due to the neglect of orbital-dependent  
 328 exchange. As a result, the VBM found by the lin-  
 329 ear method is  $\sim 0.2$  and  $\sim 0.5$  eV higher in energy  
 330 than that found by Kraut's method with DFT  
 331 for  $\alpha\text{-Fe}_2\text{O}_3$  and  $\alpha\text{-Cr}_2\text{O}_3$ , respectively. These re-  
 332 sults are similar to what was found earlier for  
 333  $\text{SrTiO}_3$ ,  $\text{TiO}_2$ , and  $\text{SrO}$  [18,19]. For the same rea-  
 334 sons as those elucidated in Refs. [18,19], we judge  
 335 the linear method to be the more reliable method  
 336 of obtaining the VBM of oxides in the absence  
 337 of more accurate self-consistent GW calculations.  
 338 Therefore, we corroborate earlier results [8] and

reaffirm that  $\Delta E_v$  for  $\alpha\text{-Cr}_2\text{O}_3$  on  $\alpha\text{-Fe}_2\text{O}_3(0001)$   
 and  $\alpha\text{-Fe}_2\text{O}_3$  on  $\alpha\text{-Cr}_2\text{O}_3(0001)$  are  $+0.7 \pm 0.1$   
 and  $-0.3 \pm 0.1$  eV, respectively.

Another question mark surrounding the band  
 offset analysis of HJs made from these materials  
 has to do with the values of the bandgaps. Once  
 $\Delta E_v$  is known, the conduction band offset is given  
 by

$$\Delta E_c = \Delta E_g - \Delta E_v \quad (2)$$

Here,  $\Delta E_g$  is the difference in bandgaps for the  
 two materials. In our prior analysis [8], we used  
 band gaps derived from optical methods  
 $-4.8 \pm 0.2$  and  $2.1 \pm 0.1$  eV for amorphous and  
 polycrystalline films of  $\alpha\text{-Cr}_2\text{O}_3$  [20] and  $\alpha\text{-Fe}_2\text{O}_3$   
 [21], respectively. We note that optical methods  
 may be influenced by the creation of bound exci-  
 tons rather than true interband transitions leading  
 to  $e^-/h^+$  pairs, which are required to drive photo-  
 chemistry in these materials. Photoconductivity is  
 a better way to measure bandgaps because one  
 can find the excitation energies at which free  
 $e^-/h^+$  pairs are created, leading to an increase in  
 conductivity at threshold. However, this method  
 does not work well for materials with low-carrier  
 mobility, such as the wide band gap semiconduct-  
 ing and insulating oxides in which we are presently  
 interested.

In the present work we have employed two  
 methods to determine bandgaps in our epitaxial  
 films—optical absorbance and core-level photo-  
 electron energy loss. We show in Fig. 5 optical  
 absorbance spectra for thick epitaxial films of  $\alpha\text{-}$   
 $\text{Cr}_2\text{O}_3$  and  $\alpha\text{-Fe}_2\text{O}_3$  grown on  $\alpha\text{-Al}_2\text{O}_3(0001)$ .  
 The absorption onset for  $\alpha\text{-Fe}_2\text{O}_3$  is at  $\sim 2.2$  eV,  
 in good agreement with previous optical results  
 [21]. However, in the absence of photoconductivity  
 measurements, we cannot know if excitation at  
 2.2 eV represents the creation of bound excitons  
 or unbound  $e^-/h^+$  pairs. The onset of absorbance  
 in the  $\alpha\text{-Cr}_2\text{O}_3$  spectrum falls at  $\sim 3.1$  eV, well be-  
 low the previously measured optical bandgap. By  
 comparing these spectral data with those obtained  
 with O 1s core-level photoemission energy loss,  
 shown in Fig. 6, we suspect that this low-energy  
 excitation corresponds to bound exciton creation.  
 In the core-level spectrum, loss intensity associated  
 with strong interband transitions above the optical

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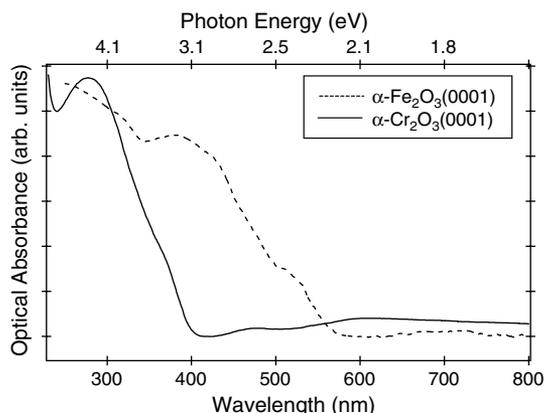


Fig. 5. Optical absorbance spectra for epitaxial films of  $\alpha$ - $\text{Cr}_2\text{O}_3$  and  $\alpha$ - $\text{Fe}_2\text{O}_3(0001)$ .

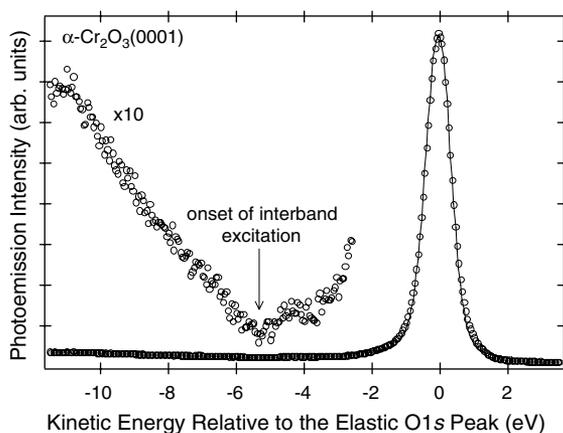


Fig. 6. O 1s core-level XPS spectrum taken at normal emission for epitaxial  $\alpha$ - $\text{Cr}_2\text{O}_3(0001)$ , including the energy loss region to low (high) kinetic (binding) energy from which the onset of interband excitation can be estimated.

387 bandgap of  $\sim 4.8$  eV is apparent. However, we also  
388 see weaker loss features between  $\sim 3$  and  $\sim 4.5$  eV,  
389 which we assign to bound exciton creation.

390 Partial densities of states projected onto Cr and  
391 O sites in  $\alpha$ - $\text{Cr}_2\text{O}_3$  reveal that the intense feature  
392 between 0 and 1 eV binding energy in the VB spec-  
393 trum of  $\alpha$ - $\text{Cr}_2\text{O}_3$  (Fig. 4b) is  $\sim 90\%$  Cr 3d  $t_{2g}$  in  
394 character. The multiple peak structure between 2  
395 and 8 eV binding energy is primarily O 2p derived.  
396 Additionally, we have been able to fit the complex  
397 multiplet structure seen in the high-resolution Cr  
398 2p core-level spectrum using an atomic multiplet

model by assuming a value of  $10Dq$  of 2.5 eV, 399  
which is in excellent agreement with the bulk value 400  
[22]. Therefore, there are unoccupied Cr 3d  $e_g$  401  
states in the gap  $\sim 1.5$ – $2.5$  eV above the VBM. 402  
Excitation of VB electrons to unoccupied states 403  
of Cr d character may account for the sub-band- 404  
gap oscillator strength observed in the optical 405  
spectrum of  $\alpha$ - $\text{Cr}_2\text{O}_3$  (Fig. 5). Nevertheless, to 406  
the best of our ability, we have confirmed that 407  
bandgap assignments of  $\sim 2.2$  and  $\sim 4.8$  eV for  $\alpha$ - 408  
 $\text{Fe}_2\text{O}_3$  and  $\alpha$ - $\text{Cr}_2\text{O}_3$ , respectively, are appropriate 409  
for our epitaxial films. As a result, the CBO values 410  
previously determined [8] are corroborated, and 411  
both HJs can be described as being of the type II 412  
or staggered band alignment. 413

#### 4. Photochemistry of TMA 414

To evaluate heterogeneous photocatalytic activ- 415  
ity at the surfaces of interest, we measured the ex- 416  
tent of photodissociation of adsorbed TMA with 417  
chopped Hg arc lamp UV light of  $\lambda \geq 385$  nm. 418  
Photodissociation of TMA on  $\text{TiO}_2(110)$  rutile 419  
has been studied in detail [1,23]. However, to the 420  
best of our knowledge, similar experiments have 421  
not been carried out on the  $\alpha$ - $\text{Cr}_2\text{O}_3$  or  $\alpha$ - 422  
 $\text{Fe}_2\text{O}_3(0001)$  surfaces, or on heterojunctions made 423  
from these materials. TMA is adsorbed by dosing 424  
the sample with TMAA, which in turn undergoes 425  
acid dissociation, leaving TMA bound to surface 426  
cations and an acid proton bound to surface O lat- 427  
tice anions. A schematic depiction of the photodis- 428  
sociation process is shown in Fig. 7. TMA is likely 429  
to sorb in a monodentate fashion, since the cation- 430  
cation spacing is too large for bidentate coordina- 431  
tion of the carboxyl functional group. TMA acts 432  
as a hole acceptor, resulting in photodissociation 433  
into  $\text{CO}_2$  and one of several other possible molec- 434  
ular fragments, as shown in Fig. 7. By using light 435  
of  $\lambda \geq 385$  nm ( $h\nu \leq 3.2$  eV), no absorption lead- 436  
ing to  $e^-/h^+$  pair creation is expected in the  $\alpha$ - 437  
 $\text{Cr}_2\text{O}_3$  layer, which is the top layer in these exper- 438  
iments. However, since 3.2 eV exceeds the band- 439  
gap of  $\alpha$ - $\text{Fe}_2\text{O}_3$ ,  $e^-/h^+$  pairs should be created in 440  
the buried  $\alpha$ - $\text{Fe}_2\text{O}_3$  layer. In principle, the holes 441  
should diffuse to the  $\alpha$ - $\text{Cr}_2\text{O}_3$  layer, since their en- 442

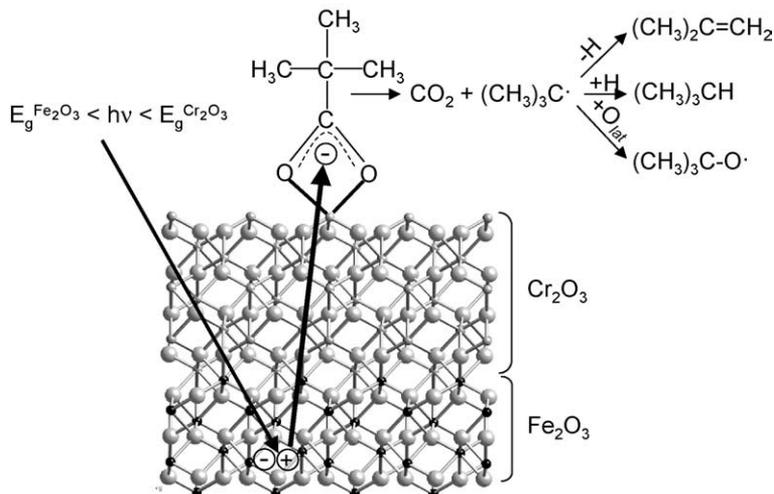


Fig. 7. Schematic drawing depicting the chemisorption of TMA at cation sites on a  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>/ $\alpha$ -Fe<sub>2</sub>O<sub>3</sub> heterojunction surface, the absorbance of UV light of photon energy less than that of  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub> but greater than that of  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>, hole diffusion to the  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub> surface, and hole-mediated photodecomposition of TMA to CO<sub>2</sub> and a butyl radical. Subsequent reactions of the butyl radical with acid protons (from dissociation of TMAA) or lattice oxygens are also shown.

443 ergy is lower there, whereas the electrons should  
444 remain in the buried  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub> layer.

445 We show in Fig. 8 high-resolution C and O 1s  
446 core-level spectra obtained at a take-off angle ( $\theta_t$ )  
447 of 12° for saturation doses of TMAA for thick-  
448 films of  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub> and  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>(0001), along with

449 those of HJs in which the top layer was  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>.  
450 All surfaces were at 300 K during dosing. The C  
451 1s spectra consist of two peaks, one for aliphatic  
452 carbon at ~284.5 eV, and one for carboxyl carbon  
453 at ~288.3 eV. The O 1s spectra exhibit an intense  
454 lattice oxygen peak at 530.0 eV, and a carboxyl

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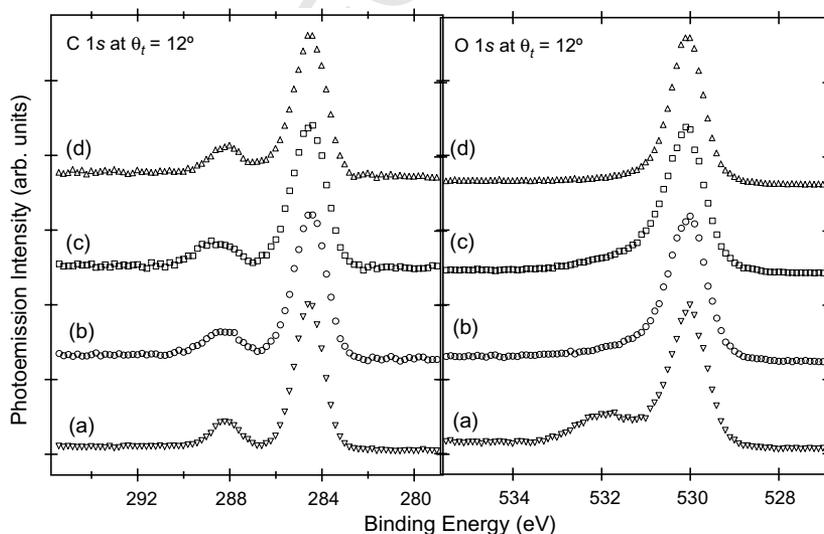


Fig. 8. C 1s (left) and O 1s (right) core-level spectra obtained at a take-off angle ( $\theta_t$ ) of 12° for saturation doses of TMA on (a)  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001), (b) 2 ML  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>/ $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001), (c) 10 ML  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>/ $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001), and (d) 350 ML  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>/ $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001).

455 peak at  $\sim 532$  eV, which is clearly visible only  
 456 on the pure  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001) surface. TMA on  
 457  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>(0001), in either thick or thin film form,  
 458 results in a much weaker carboxyl O 1s feature  
 459 with a smaller chemical shift relative to the lattice  
 460 O peak. The spectra have been normalized to a  
 461 constant height. Therefore, it is not apparent from  
 462 Fig. 8 that TMA uptake is much greater on  $\alpha$ -  
 463 Fe<sub>2</sub>O<sub>3</sub> than on  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>. We estimate the absolute  
 464 TMA coverage on the various surfaces the follow-  
 465 ing way. Starting with the  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001) surface,  
 466 we reference the carboxyl O 1s peak area to the lat-  
 467 tice O 1s peak area by noting that the lattice O 1s  
 468 intensity can be written as

$$I_{\text{lat}}(\theta_t) = \sum_j I_j(\theta_t) = I_o \sum_j \exp(-d_j/\lambda \sin \theta_t) \quad (3)$$

472 Here, we sum over layers of closed-packed O  
 473 anions assuming a continuum model for the materi-  
 474 al characterized by an electron attenuation  
 475 length,  $\lambda$ , and O layer depths below the surface  
 476 of  $d_j$ . Photoelectron diffraction effects are ignored.  
 477  $I_o$  is the O 1s intensity from the topmost layer of O  
 478 anions. The TMA carboxyl O 1s peak intensity  
 479 after sorption on  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001) can be written as,

$$I_{\text{TMA}}(\theta_t) = fI_o \quad (4)$$

483 where  $f$  is the TMA oxygen fractional coverage in  
 484 units of a ML of close-packed lattice O. Combin-  
 485 ing Eqs. (3) and (4) yields,

$$\ln(f) = \ln \sum_j \exp(-d_j/\lambda \sin \theta_t) + \ln[I_{\text{TMA}}(\theta_t)/I_{\text{lat}}(\theta_t)] \quad (5)$$

488 The first term on the right is computed for rea-  
 489 sonable values of attenuation length, and the sec-  
 490 ond term contains the measured peak areas from  
 491 the O 1s spectrum for  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001). The TMA  
 492 coverage referenced to the cation density on the  
 493 surface of  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001),  $\theta_{\text{TMA}}^{\text{Fe}_2\text{O}_3}$ , is then  
 494  $3.0(0.5f) = 1.5f$ . Here, we note that the factor of  
 495 0.5 stems from the fact that there are two oxygens  
 496 per TMA anion, and the factor of 3.0 from the fact  
 497 that the  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001) surface is terminated with  
 498 1/3 ML of Fe cations [12]. Finally, the TMA cov-  
 499 erage on the  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>(0001) surface,  $\theta_{\text{TMA}}^{\text{Cr}_2\text{O}_3}$ , can  
 500 be related to  $\theta_{\text{TMA}}^{\text{Fe}_2\text{O}_3}$  by the formula,

$$\theta_{\text{TMA}}^{\text{Cr}_2\text{O}_3} = \theta_{\text{TMA}}^{\text{Fe}_2\text{O}_3} [I_{\text{C } 1s}^{\text{Cr}_2\text{O}_3}(\theta_t)/I_{\text{C } 1s}^{\text{Fe}_2\text{O}_3}(\theta_t)] \quad (6)$$

where  $I_{\text{C } 1s}^{\text{Cr}_2\text{O}_3}(\theta_t)$  and  $I_{\text{C } 1s}^{\text{Fe}_2\text{O}_3}(\theta_t)$  are the total C1s areas  
 503 under both aliphatic and carboxyl peaks on the  $\alpha$ -  
 504 Cr<sub>2</sub>O<sub>3</sub>(0001) and  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001) surfaces, respec-  
 505 tively. Using  $\lambda = 12 \pm 3$  Å, we arrive at  $\theta_{\text{TMA}}^{\text{Fe}_2\text{O}_3} =$   
 506  $1.1 \pm 0.2$  ML and  $\theta_{\text{TMA}}^{\text{Cr}_2\text{O}_3} = 0.3 \pm 0.2$  ML. The  
 507 lower TMA coverage on the  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>(0001)  
 508 surfaces is most likely due to a partial chromyl ter-  
 509 mination [13], which is expected to block cation  
 510 sites from chemisorption of other species at  
 511 300 K [24]. We draw this conclusion based on  
 512 the fact that subsequent UHV annealing of the  
 513  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>(0001) to drive off the TMA, followed by  
 514 readsorption of TMAA, invariably results in an in-  
 515 crease in TMAA uptake, presumably as a result of  
 516 removal of some of the chromyl termination.  
 517

518 We now examine the photodesorption products  
 519 of TMA from these different surfaces. We moni-  
 520 tored mass 44 (CO<sub>2</sub>), 41 (C<sub>3</sub>H<sub>5</sub>—a mass fragment  
 521 common to all three final products depicted in Fig.  
 522 7), and mass 18 (H<sub>2</sub>O) as a function of time before,  
 523 during and after a 60 s UV light exposure at  
 524  $\lambda \geq 385$  nm, with the surface at 300 K. The result-  
 525 ing traces typically look like that shown in Fig. 9,  
 526 which were taken for 10 ML  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub> on  $\alpha$ -  
 527 Fe<sub>2</sub>O<sub>3</sub>(0001). Masses 44 and 41 rise as soon as  
 528 the light shutter is opened at  $t = 0$ , and either  
 529 slightly decay, or remain constant during the irra-

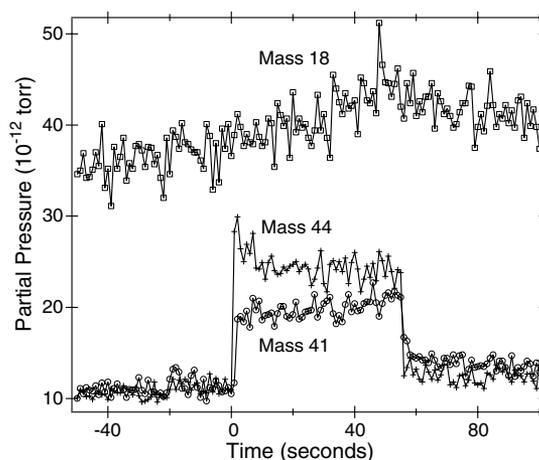


Fig. 9. Desorption yields for masses 18, 44, and 41 from 10 ML  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>/ $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001) using chopped Hg arc lamp UV light with a 385 nm cut-off filter.

530 diation period, and then drop immediately when  
531 the light shutter is closed. The instantaneous re-  
532 sponse indicates that these are photodesorption  
533 as opposed to thermal desorption products. In  
534 contrast, the mass 18 peak rises slowly after open-  
535 ing the light shutter, as expected for a thermal  
536 desorption product arising from UV heating of  
537 the sample. The lack of signal fall off throughout  
538 light exposure for masses 41 and 44 is most likely  
539 due to accumulation of charge as a result of the  
540 insulating nature of these materials, as well as a  
541 slight thermal contribution due to sample heating.  
542 Internal charging in the surface or HJ is expected if  
543 the TMA scavenges the holes, and the material is  
544 not sufficiently conductive to conduct away the  
545 electrons.

546 The dependence of the extent of photodesorp-  
547 tion on  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub> layer thickness in HJs is shown  
548 in Fig. 10. Here we plot the mass 44 signal,  
549 normalized to the amount of TMA on the surface,  
550 vs. time for: (a) thick-film  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001), (b) 2 ML  
551  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>, (c) 10 ML  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>, and (d) 350 ML  
552  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>, all on thick-film  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001). The  
553 photoresponse of the  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001) surface is  
554 rather slight, even though the UV light energy ex-  
555 ceeds the bandgap. Nonradiative recombination of

556  $e^-/h^+$  pairs at the surface or hole trapping in d  
557 states in the gap may be responsible for this result.  
558 Moving to the HJs, the photoresponse is larger for  
559 2 and 10 ML of  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub> on  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001) than it  
560 is for pure  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>, and the response is approxi-  
561 mately the same for these two HJs. Taken at face  
562 value, this result suggests that the HJ promotes  
563 hole-mediated decomposition of TMA, possibly  
564 through  $e^-/h^+$  pair separation via a staggered band  
565 alignment. In order to test this idea, we examine  
566 the photoresponse of a much thicker  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub> layer  
567 (350 ML, or  $\sim 800$  Å). In this case, the light is ex-  
568 pected to penetrate to the buried HJ where it will  
569 be absorbed. However, it is not anticipated that  
570 the hole will be able to readily diffuse to the surface  
571 because of the very high resistivity of epitaxial  $\alpha$ -  
572 Cr<sub>2</sub>O<sub>3</sub>. Surprisingly, a photoresponse is still pres-  
573 ent at 350 ML (Fig. 10d). This result reveals that  
574 an excitation leading to photochemical decomposi-  
575 tion of TMA is able to occur, even though the UV  
576 light energy is less than the bandgap of  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>.  
577 One way this phenomenon could happen is  
578 through creation of a bound exciton at the surface  
579 which affects the stability of the bonds in the TMA  
580 species. As seen in Fig. 5, there is weak optical  
581 absorption in  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub> at 385 nm, presumably  
582 due to dipole allowed O 2p to Cr 3d or weak Cr  
583 d–d transitions that become allowed by admixture  
584 with O 2p states. Both transitions are expected to  
585 lead to bound exciton formation. Inasmuch as  
586 these excitations change the valence electron distri-  
587 bution in surface Cr cations, the C–C bond in  
588 TMA between the *t*-butyl and carboxylate groups  
589 may be weakened to the point that decomposition  
590 occurs. This unexpected and interesting result will  
591 be more thoroughly explored in future work.

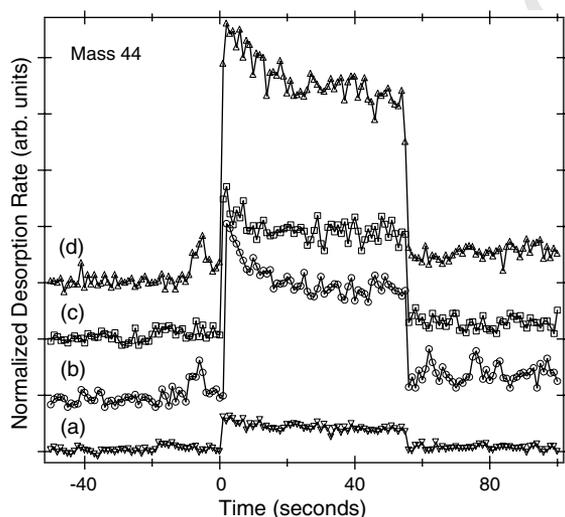


Fig. 10. Mass 44 photodesorption yield using chopped Hg arc lamp UV light with a 385 nm cut-off filter for (a)  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001), (b) 2 ML  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>/ $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001), (c) 10 ML  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>/ $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001), and (d) 350 ML  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>/ $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001).

## 5. Summary

592 We have investigated the possibility that elec-  
593 tron–hole pair creation and separation, via stag-  
594 gered band alignment at an oxide/oxide  
595 heterojunction, might enhance photochemical  
596 decomposition of an adsorbed molecule. Our test  
597 case was hole-mediated photodecomposition of  
598 trimethyl acetate on well-defined epitaxial hetero-  
599 junctions of  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>(0001) on  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>(0001)  
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601 using UV light of energy intermediate between the  
 602 bandgaps of the two oxides. There is no obvious  
 603 effect of the staggered band alignment on the pho-  
 604 tochemical process. Rather, photochemical  
 605 decomposition is more extensive on  $\alpha$ -Cr<sub>2</sub>O<sub>3</sub>, for  
 606 which the exciting light is not sufficiently energetic  
 607 to create electron–hole pairs, than it is on  $\alpha$ -Fe<sub>2</sub>O<sub>3</sub>,  
 608 for which the light energy exceeds the bandgap.  
 609 We suggest that this interesting and unanticipated  
 610 effect may be driven by the creation of bound exci-  
 611 tons which lead to photodecomposition of the  
 612 adsorbate. We plan to investigate this phenome-  
 613 non in more detail in the future.

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 630 00OR22725.

#### 631 References

632 [1] J.M. White, J. Szanyi, M.A. Henderson, J. Phys. Chem. B.  
 633 107 (2003) 2009.

- [2] See, for example M. Anpo, M. Takeuchi, J. Catal. 216 634  
 (2003) 505. 635  
 [3] S. Thiel, T. Kluner, M. Wilde, K. Al-Shamery, H.J. 636  
 Freund, Chem. Phys. 228 (1998) 185. 637  
 [4] J. Bandara, J.A. Mielczarski, A. Lopez, J. Kiwi, Appl. 638  
 Catal. B—Environ. 34 (2001) 321. 639  
 [5] M.A. Gondal, A. Hameed, Z.H. Yamani, A. Suwaiyan, 640  
 Appl. Catal. A—Gen. 268 (2004) 159. 641  
 [6] J. Shang, Y.F. Zhu, Z.L. Xu, L.Q. Jing, Y.G. Du, Chinese 642  
 J. Catal. 24 (2003) 369. 643  
 [7] S. Sakthivel, S.-U. Geissen, D.W. Bahnemann, V. Murug- 644  
 esan, A.J. Vogelpohl, J. Photochem. Photobiol. A 148 645  
 (2002) 283. 646  
 [8] S.A. Chambers, Y. Liang, Y. Gao, Phys. Rev. B. 61 (2000) 647  
 13223. 648  
 [9] J.E. Jaffe, M. Dupuis, M. Gutowski, Phys. Rev. B. 69 649  
 (2004) 205106. 650  
 [10] A. Francioso, C.G. Van de Walle, Surf. Sci. Rep. 25 (1996) 651  
 1. 652  
 [11] S.A. Chambers, Surf. Sci. Rep. 39 (2000) 105. 653  
 [12] S.A. Chambers, S.I. Yi, Surf. Sci. 439 (1999) L785. 654  
 [13] B. Dillmann et al., Faraday Discuss. 105 (1997) 295. 655  
 [14] S.A. Chambers, The chemical physics of solid surfaces, in: 656  
 D.P. Woodruff (Ed.), Oxide Surfaces, vol. 9, Elsevier, 657  
 Amsterdam, 2001 (Chapter 7). 658  
 [15] R.A. McKee, F.J. Walker, M.B. Nardelli, W.A. Shelton, 659  
 G.M. Stocks, Science 300 (2003) 1726. 660  
 [16] E.A. Kraut, R.W. Grant, J.R. Waldrop, S.P. Kowalczyk, 661  
 Phys. Rev. Lett. 44 (1980) 1620. 662  
 [17] E.A. Kraut, R.W. Grant, J.R. Waldrop, S.P. Kowalczyk, 663  
 Phys. Rev. B 28 (1983) 1965. 664  
 [18] S.A. Chambers, T. Droubay, T.C. Kasper, M. Gutowski, 665  
 M. van Schilfgaard, Surf. Sci. 554 (2004) 81. 666  
 [19] S.A. Chambers, T. Droubay, T.C. Kasper, M. Gutowski, 667  
 J. Vac. Sci. Technol. B 22 (2004) 2205. 668  
 [20] S. Hong, E. Kim, D.-W. Kim, T.-H. Sung, K. No, J. Non- 669  
 Cryst. Sol. 221 (1997) 245. 670  
 [21] S. Mohanty, J. Ghose, J. Phys. Chem. Solids 53 (1992) 81. 671  
 [22] S.A. Chambers, T. Droubay, Phys. Rev. B 64 (2001) 672  
 075410. 673  
 [23] M.A. Henderson, J.M. White, H. Uetska, H. Onishi, J. 674  
 Amer. Chem. Soc. 125 (2003) 14974. 675  
 [24] M.A. Henderson, S.A. Chambers, Surf. Sci. 449 (2000) 676  
 135. 677  
 678